

Notice of References Cited

Application/Control No.

09/536,927

Applicant(s)/Patent Under
Reexamination
HAWRYLUK ET AL.

Examiner

Toniae M. Thomas

Art Unit

2822

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,238,587 B1	05-2001	Siniaguine et al.	216/59
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kramer et al., "Characterization of Reverse Leakage Components for Ultrashallow p+/n Diodes Fabricated Using Gas Immersion Laser Doping," IEEE Electron Device Letters, Vol. 17, No. 10, October 1996, pages 461-463.
	V	
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	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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